

**TOSHIBA**

**TLP759F**

TOSHIBA PHOTOCOUPLER GaAlAs IRED + PHOTO-IC

# TLP759F

DIGITAL LOGIC GROUND ISOLATION

LINE RECEIVER

MICROPROCESSOR SYSTEM INTERFACES

SWITCHING POWER SUPPLY FEEDBACK CONTROL

TRANSISTOR INVERTOR

The TOSHIBA TLP759F consists of a GaAlAs high-output light emitting diode and a high speed detector of one chip photo diode-transistor. This unit is 8-lead DIP package.

TLP759F has no internal base connection, and a Faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

So this is suitable for application in noisy environmental condition. All parameters are tested to the specification of TLP759.

- Isolation Voltage : 5000 Vrms (Min.)
- Switching Speed :  $t_{pHL} = 0.3\mu s$  (Typ.)  
 $t_{pLH} = 0.5\mu s$  (Typ.) ( $R_L = 1.9k\Omega$ )
- TTL Compatible
- UL Recognized : UL1577, File No. E67349
- Option (D4) type  
VDE Approved : DIN VDE0884 / 06.92  
Certificate No. 83676

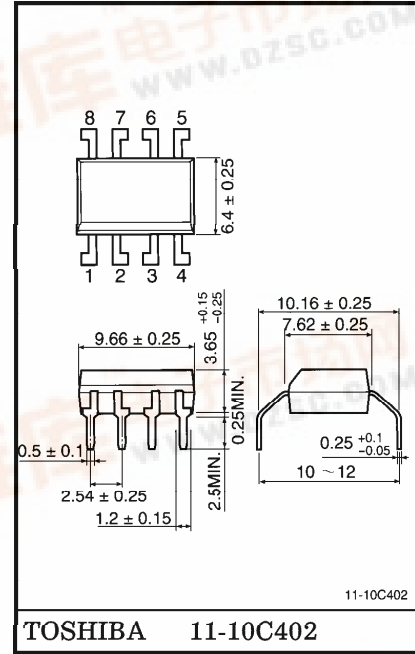
Maximum Operating Insulation : 1140V<sub>PK</sub>

Highest Permissible Over Voltage : 6000V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

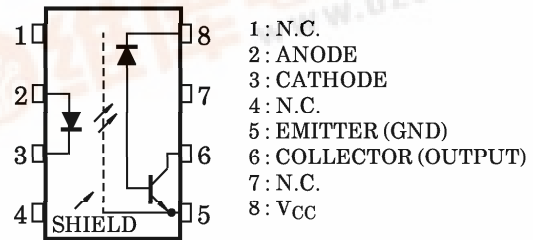
- Creepage Distance : 8.0mm
- Clearance : 8.0mm
- Insulation Thickness : 0.4mm

Unit in mm

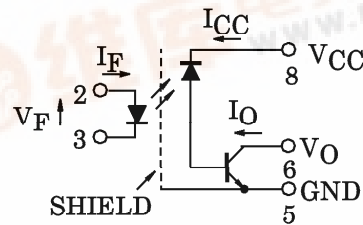


Weight : 0.54g

### PIN CONFIGURATION (TOP VIEW)



### SCHEMATIC



961001EBC2

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